Showerhead

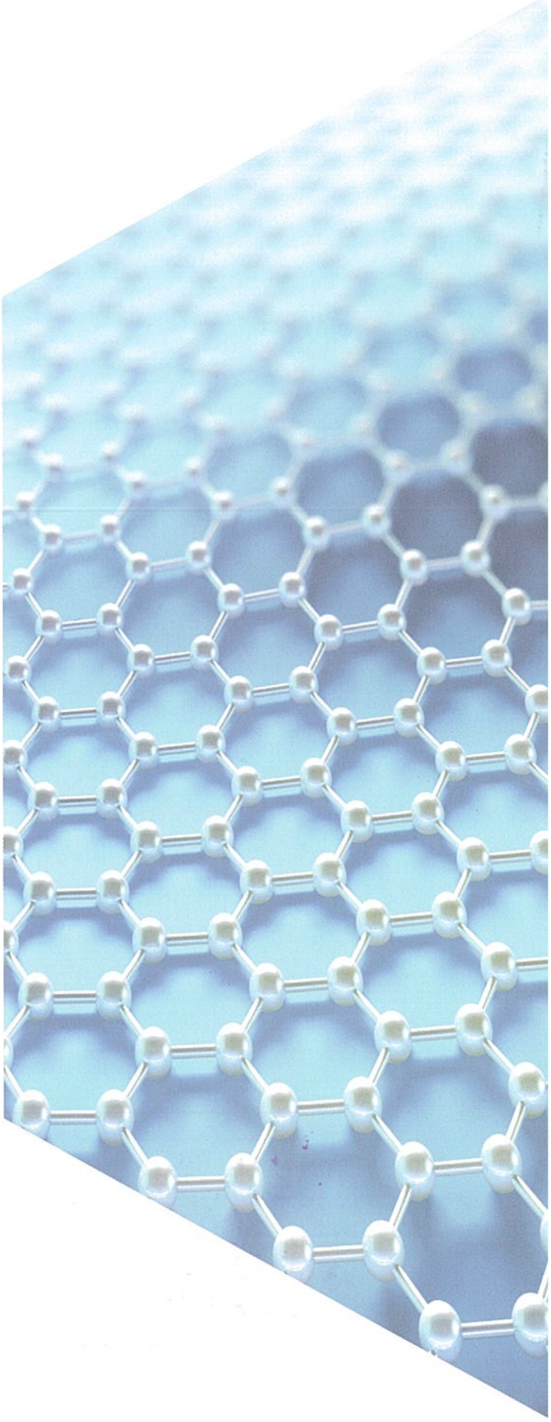
ATOMIC PREMIUM

Available from 4"to 12" wafer

Thermal & Plasma Enhanced ALD Process

System Specification

Substrate Size : 4 ~ 12" Standard (Wafer)
Thermal ALD Process (Plasma Process Available)
Chamber Material : Al6061 with Anodized
Gap Adjustable between Showerhead and Substrate
Gas Delivery System : Bubbler, LDS etc.
Max Temperature : 500℃ (@ Wafer)
No. of Precursor Canisters : Up to 4 Sets (Standard)
Pressure Control : Automatic Control by Throttle Valve
Process Gauge : CDG Gauge (10 Torr)
Process Pump : Dry Pump (Rotary Pump Available)
Pumping Line Hot Trap to Reduce Particle



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